

| 37 CFR 1.501 INFORMATION DISCLOSURE STATEMENT IN A PATENT (use several sheets if necessary) | | | | | Docket No. 09792909-5625 | Serial No. | | |
|---|----|---|----------|-----------------|-----------------------------------|----------------|----------------------------|----|
| | | | | | Applicants: Osamu Goto, et al. | | | |
| | | | | | Filing Date June 25, 2003 | Group Art Unit | | |
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| Examiner's Initials | | Document Number | Date | Name | Class | Subclass | Filing Date If appropriate | |
| ON | AA | 6,060,335 | 5-9-00 | Rennie | | | | |
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| | | Document Number | Date | Country | Class | Subclass | Yes | No |
| ON | AH | JP11-54794 | 2-26-99 | Japan | | | Abstract | |
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| OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | | | |
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| Examiner | | ON | | Date Considered | | 9/21/04 | | |
| *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | | | | | | | |